

Rafal Jakiela

List of Publications by Year in descending order

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208
papers

2,847
citations

236612

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all docs

211
docs citations

211
times ranked

3130
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of beryllium diffusion in HVPE-GaN grown in [11 $\bar{2}$ 0] and [10-10] crystallographic directions. <i>Materials Science in Semiconductor Processing</i> , 2022, 139, 106332.	1.9	3
2	Effect of rapid thermal annealing on short period {CdO/ZnO} _m SLs grown on m-Al ₂ O ₃ . <i>Materials Science in Semiconductor Processing</i> , 2022, 142, 106493.	1.9	4
3	Hydrogen in As \bar{c} Grown and Annealed ZnO Films Grown by Atomic Layer Deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000318.	0.8	5
4	Effects of MOVPE Growth Conditions on GaN Layers Doped with Germanium. <i>Materials</i> , 2021, 14, 354.	1.3	14
5	Influence of As doping on the properties of nonpolar ZnO. <i>Thin Solid Films</i> , 2021, 720, 138520.	0.8	4
6	Accumulation of Arsenic Implantation-Induced Donor Defects in Hg _{0.7} Cd _{0.3} Te Heteroepitaxial Structures. <i>Journal of Electronic Materials</i> , 2021, 50, 3714-3721.	1.0	0
7	Correlation between electrical conductivity and luminescence properties in $\bar{1}^2$ -Ga ₂ O ₃ :Cr ³⁺ and $\bar{1}^2$ -Ga ₂ O ₃ :Cr,Mg single crystals. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	0.9	22
8	Analysis of carrier species in arsenic-implanted p- and n-type Hg _{0.7} Cd _{0.3} Te. <i>Infrared Physics and Technology</i> , 2021, 114, 103665.	1.3	1
9	Schottky contacts to ZnO layers grown by Atomic Layer Deposition: effects of H ₂ O ₂ functionalization and transport mechanisms. <i>Applied Surface Science</i> , 2021, 552, 149067.	3.1	3
10	Solubility limits of vanadium in CdTe and (Cd,Mn)Te crystals. <i>Journal of Crystal Growth</i> , 2021, 563, 126094.	0.7	1
11	Improved-sensitivity integral SQUID magnetometry of (Ga,Mn)N thin films in proximity to Mg-doped GaN. <i>Journal of Alloys and Compounds</i> , 2021, 868, 159119.	2.8	8
12	Structural Properties of Thin ZnO Films Deposited by ALD under O-Rich and Zn-Rich Growth Conditions and Their Relationship with Electrical Parameters. <i>Materials</i> , 2021, 14, 4048.	1.3	19
13	CdTe-based crystals with Mg, Se, or Mn as materials for X and gamma ray detectors: Selected physical properties. <i>Progress in Crystal Growth and Characterization of Materials</i> , 2021, 67, 100543.	1.8	10
14	Improving the Properties of Composite Titanium Nitride Layers on the AZ91D Magnesium Alloy Using Hydrothermal Treatment. <i>Materials</i> , 2021, 14, 5903.	1.3	4
15	SIMS accurate determination of matrix composition of topological crystalline insulator material Pb _{1-x} Sn _x Se. <i>Surface and Interface Analysis</i> , 2020, 52, 71-75.	0.8	3
16	High Pressure Processing of Ion Implanted GaN. <i>Electronics (Switzerland)</i> , 2020, 9, 1380.	1.8	36
17	Nano-size defect layers in arsenic-implanted and annealed HgCdTe epitaxial films studied with transmission electron microscopy. <i>Applied Nanoscience (Switzerland)</i> , 2020, 10, 4971-4976.	1.6	5
18	Investigation of diffusion mechanism of beryllium in GaN. <i>Physica B: Condensed Matter</i> , 2020, 594, 412316.	1.3	8

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19	GaAs _{1-x} Bix growth on Ge: anti-phase domains, ordering, and exciton localization. Scientific Reports, 2020, 10, 2002.	1.6	10
20	Influence of oxygen-rich and zinc-rich conditions on donor and acceptor states and conductivity mechanism of ZnO films grown by ALD—Experimental studies. Journal of Applied Physics, 2020, 127, .	1.1	22
21	Conductance spectra of (Nb, Pb, In)/NbP superconductor/Weyl semimetal junctions. Physical Review B, 2020, 101, .	1.1	9
22	Detection of Si doping in the AlN/GaN MQW using Super X “ EDS measurements. Micron, 2020, 134, 102864.	1.1	3
23	The Role of Atmospheric Elements in the Wide Band-Gap Semiconductors. Acta Physica Polonica A 136, 916 (2019), ERRATUM. Acta Physica Polonica A, 2020, 137, 437-438.	0.2	0
24	Role of intrinsic and extrinsic defects in H implanted hydrothermally grown ZnO. Journal of Applied Physics, 2019, 126, 125707.	1.1	10
25	ZnO:Sb MBE layers with different Sb content—optical, electronic and structural analysis. Journal of Alloys and Compounds, 2019, 797, 1163-1172.	2.8	9
26	Evidence for the homogeneous ferromagnetic phase in (Ga,Mn)(Bi,As) epitaxial layers from muon spin relaxation spectroscopy. Scientific Reports, 2019, 9, 3394.	1.6	8
27	Comparison of defect structure in Si and Ge ion implanted GaN epilayers by RBS/channeling. Nuclear Instruments & Methods in Physics Research B, 2019, 444, 74-79.	0.6	5
28	Structural and Electrical Parameters of ZnO Thin Films Grown by ALD with either Water or Ozone as Oxygen Precursors. Crystals, 2019, 9, 554.	1.0	13
29	Diffusion of Mn in gallium nitride: Experiment and modelling. Journal of Alloys and Compounds, 2019, 771, 215-220.	2.8	13
30	Analysis of defect structure in GaN epilayers doped with implanted Si ⁺ by RBS/c method. Nuclear Instruments & Methods in Physics Research B, 2019, 450, 248-251.	0.6	5
31	The Role of Atmospheric Elements in the Wide Band-Gap Semiconductors. Acta Physica Polonica A, 2019, 136, 916-939.	0.2	6
32	Electronic phase separation in insulating (Ga, Mn) As with low compensation: super-paramagnetism and hopping conduction. Journal of Physics Condensed Matter, 2018, 30, 095801.	0.7	5
33	Deep levels in the MBE ZnO:As/n-GaN diodes “ Photoluminescence, electrical properties and deep level transient spectroscopy. Journal of Alloys and Compounds, 2018, 742, 296-303.	2.8	10
34	Impact of substrate temperature on magnetic properties of plasma-assisted molecular beam epitaxy grown (Ga,Mn)N. Journal of Alloys and Compounds, 2018, 747, 946-959.	2.8	18
35	Hydrogen diffusion in GaN:Mg and GaN:Si. Journal of Alloys and Compounds, 2018, 747, 354-358.	2.8	24
36	Investigation of Cd $1\hat{x}$ Mg x Te as possible materials for X and gamma ray detectors. Journal of Crystal Growth, 2018, 491, 73-76.	0.7	8

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37	Compositional, structural, and optical properties of atomic layer deposited tantalum oxide for optical fiber sensor overlays. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, .	0.9	7
38	Band structure evolution and the origin of magnetism in (Ga,Mn)As: From paramagnetic through superparamagnetic to ferromagnetic phase. <i>Physical Review B</i> , 2018, 97, .	1.1	24
39	Electrical isolation of GaAs and AlGaAs/GaAs Quantum Cascade Lasers by deep hydrogen implantation. <i>Materials Science in Semiconductor Processing</i> , 2018, 74, 88-97.	1.9	2
40	Comprehensive investigation of the interfacial misfit array formation in GaSb/GaAs material system. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1.	1.1	11
41	Semiconductor crystals based on CdTe with Se – Some structural and optical properties. <i>Journal of Crystal Growth</i> , 2018, 498, 405-410.	0.7	6
42	Experimental and theoretical analysis of influence of barrier composition on optical properties of GaN/AlGaIn multi-quantum wells: Temperature- and pressure-dependent photoluminescence studies. <i>Journal of Alloys and Compounds</i> , 2018, 769, 1064-1071.	2.8	9
43	Ultrahigh sensitivity SIMS analysis of oxygen in silicon. <i>Surface and Interface Analysis</i> , 2018, 50, 729-733.	0.8	10
44	Nematicity of correlated systems driven by anisotropic chemical phase separation. <i>Physical Review Materials</i> , 2018, 2, .	0.9	9
45	Investigation of Co Ions Diffusion in Gd ₃ Ga ₅ O ₁₂ Single Crystals. <i>Acta Physica Polonica A</i> , 2018, 133, 959-964.	0.2	2
46	Fermi level and bands offsets determination in insulating (Ga,Mn)N/GaN structures. <i>Scientific Reports</i> , 2017, 7, 41877.	1.6	23
47	X-ray photoelectron spectroscopy study of highly-doped ZnO:Al,N films grown at O-rich conditions. <i>Journal of Alloys and Compounds</i> , 2017, 722, 683-689.	2.8	27
48	Spatial distribution of optical coloration in single crystalline LiNbO ₃ after high-temperature H ₂ /air treatments. <i>Optical Materials</i> , 2017, 70, 106-115.	1.7	12
49	Structure-property relationships in ZnO:Al-hydroquinone films grown on flexible substrates by atomic and molecular layer deposition. <i>Materials and Design</i> , 2017, 119, 297-302.	3.3	12
50	Optical and electrical studies of arsenic-implanted HgCdTe films grown with molecular beam epitaxy on GaAs and Si substrates. <i>Infrared Physics and Technology</i> , 2017, 81, 52-58.	1.3	21
51	Diversity of contributions leading to the nominally n-type behavior of ZnO films obtained by low temperature Atomic Layer Deposition. <i>Journal of Alloys and Compounds</i> , 2017, 727, 902-911.	2.8	19
52	Properties of arsenic-implanted Hg _{1-x} Cd _x Te MBE films. <i>EPJ Web of Conferences</i> , 2017, 133, 01001.	0.1	0
53	The use of high-mass clusters to measure the TOF SIMS profiles of implanted bismuth. <i>International Journal of Mass Spectrometry</i> , 2017, 422, 143-145.	0.7	1
54	Infrared Reflectance Analysis of Epitaxial n-Type Doped GaN Layers Grown on Sapphire. <i>Nanoscale Research Letters</i> , 2017, 12, 397.	3.1	5

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55	Tuning the properties of ALD-ZnO-based rectifying structures by thin dielectric film insertion – Modeling and experimental studies. <i>Journal of Alloys and Compounds</i> , 2017, 693, 1164-1173.	2.8	4
56	Interplay between localization and magnetism in (Ga,Mn)As and (In,Mn)As. <i>Physical Review Materials</i> , 2017, 1, .	0.9	28
57	Proton implantation for the isolation of AlGaAs/GaAs quantum cascade lasers. <i>Semiconductor Science and Technology</i> , 2016, 31, 075010.	1.0	7
58	N and Al co-doping as a way to p-type ZnO without post-growth annealing. <i>Materials Research Express</i> , 2016, 3, 125907.	0.8	9
59	The chemical states of As 3d in highly doped ZnO grown by Molecular Beam Epitaxy and annealed in different atmospheres. <i>Thin Solid Films</i> , 2016, 605, 283-288.	0.8	9
60	The importance of structural inhomogeneity in GaN thin films. <i>Journal of Crystal Growth</i> , 2016, 456, 160-167.	0.7	3
61	Observation of surface states on heavily indium-doped SnTe(111), a superconducting topological crystalline insulator. <i>Physical Review B</i> , 2016, 93, .	1.1	27
62	Stretching magnetism with an electric field in a nitride semiconductor. <i>Nature Communications</i> , 2016, 7, 13232.	5.8	33
63	Arsenic chemical state in MBE grown epitaxial ZnO layers – doped with As, N and Sb. <i>Journal of Alloys and Compounds</i> , 2016, 687, 937-942.	2.8	11
64	Polarity dependence of Mn incorporation in (Ga,Mn)N superlattices. <i>Journal of Crystal Growth</i> , 2016, 437, 49-52.	0.7	1
65	Structural properties and metallic conductivity of Ti _{1-x} Nb _x O ₂ films grown by atomic layer deposition on crystalline substrates. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 495305.	1.3	3
66	Composite titanium nitride layers produced on the AZ91D magnesium alloy by a hybrid method including hydrothermal modification of the layer. <i>Applied Surface Science</i> , 2015, 346, 394-405.	3.1	10
67	Incorporation of oxygen in SiC implanted with hydrogen. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2015, 365, 146-149.	0.6	4
68	Magnetic, optical and electrical characterization of SiC doped with scandium during the PVT growth. <i>Journal of Crystal Growth</i> , 2015, 413, 86-93.	0.7	13
69	Processing of AlGaAs/GaAs quantum-cascade structures for terahertz laser. <i>Journal of Nanophotonics</i> , 2015, 9, 093079.	0.4	6
70	Electron beam induced current profiling of the p-ZnO:N-GaN heterojunction. <i>Applied Physics Letters</i> , 2015, 106, .	1.5	14
71	Nitrogen doped p-type ZnO films and p-n homojunction. <i>Semiconductor Science and Technology</i> , 2015, 30, 015001.	1.0	27
72	Response of ZnO/GaN Heterostructure to Ion Irradiation. <i>Acta Physica Polonica A</i> , 2015, 128, 832-835.	0.2	0

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73	PA-MBE Grown p-n (p-ZnO:(As+Sb)/i>n</i>-GaN) and p-i-n (p-ZnO:As/HfO₂/n-GaN) Heterojunctions as a Highly Selective UV Detectors. Key Engineering Materials, 2014, 605, 310-313.	0.4	2
74	Processing of AlGaAs/GaAs QC structures for terahertz laser. , 2014, , .		1
75	Diffusion and impurity segregation in hydrogen-implanted silicon carbide. Journal of Applied Physics, 2014, 115, .	1.1	26
76	Influence of annealing on the properties of (Cd,Mn)Te crystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1528-1532.	0.8	4
77	High resistivity isolation for AlGaIn/GaN HEMT using Al double-implantation. Materials Research Society Symposia Proceedings, 2014, 1635, 9-14.	0.1	2
78	Electrical and structural characterization of nitrogen doped ZnO layers grown at low temperature by atomic layer deposition. Semiconductor Science and Technology, 2014, 29, 085006.	1.0	4
79	Electrical and mechanical stability of aluminum-doped ZnO films grown on flexible substrates by atomic layer deposition. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2014, 186, 15-20.	1.7	22
80	Atomic layer deposition of Zn _{1-x} Mg _x O:Al transparent conducting films. Journal of Materials Science, 2014, 49, 1512-1518.	1.7	12
81	Thermal stability of multilayer Ti ₂ AlN-based ohmic contacts to n-GaN in ambient air. Solid-State Electronics, 2014, 94, 15-19.	0.8	5
82	Dual-acceptor doped p-n-ZnO:(As,Sb)/n-GaN heterojunctions grown by PA-MBE as a spectrum selective ultraviolet photodetector. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 2072-2077.	0.8	17
83	Dominant shallow donors in zinc oxide layers obtained by low-temperature atomic layer deposition: Electrical and optical investigations. Acta Materialia, 2014, 65, 69-75.	3.8	20
84	Growth of SiC by PVT method with different sources for doping by a cerium impurity, CeO ₂ or CeSi ₂ . Journal of Crystal Growth, 2014, 401, 677-680.	0.7	5
85	XPS study of arsenic doped ZnO grown by Atomic Layer Deposition. Journal of Alloys and Compounds, 2014, 582, 594-597.	2.8	25
86	Photo-etching of HVPE-grown GaN: Revealing extended non-homogeneities induced by periodic carrier gas exchange. Journal of Crystal Growth, 2014, 403, 77-82.	0.7	8
87	Growth and Characterization of (Cd, Mn)Te. IEEE Transactions on Nuclear Science, 2013, 60, 3805-3814.	1.2	7
88	Homogeneous and heterogeneous magnetism in (Zn,Co)O: From a random antiferromagnet to a dipolar superferromagnet by changing the growth temperature. Physical Review B, 2013, 88, .	1.1	43
89	Relation between exciton splittings, magnetic circular dichroism, and magnetization in wurtzite Ga _{1-x} Fe _x N. Physical Review B, 2013, 88, .	1.1	8
90	Phase diagram and critical behavior of the random ferromagnet Ga _{1-x} Mn _x N. Physical Review B, 2013, 88, .	1.1	5

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91	Growth of SiC by PVT method in the presence of cerium dopant. Journal of Crystal Growth, 2013, 377, 88-95.	0.7	5
92	Characteristics of ZnO ϵ As/GaN heterojunction diodes obtained by PA-MBE. Journal Physics D: Applied Physics, 2013, 46, 035101.	1.3	19
93	Structural and Electrical Properties of SiC Grown by PVT Method in the Presence of the Cerium Vapor. Acta Physica Polonica A, 2013, 124, 761-764.	0.2	1
94	Effect of Nitrogen Doping on the Growth of 4H Polytype on the 6H-SiC Seed by PVT Method. Materials Science Forum, 2012, 717-720, 29-32.	0.3	5
95	Homogenous and heterogeneous magnetism in (Zn,Co)O. , 2012, , .		1
96	Effect of Stress on Structural Transformations in GaMnAs. Journal of Nanoscience and Nanotechnology, 2012, 12, 8721-8724.	0.9	0
97	Manipulating Mn ϵ Mg ϵ cation complexes to control the charge- and spin-state of Mn in GaN. Scientific Reports, 2012, 2, 722.	1.6	43
98	Ga ϵ xMn ϵ N epitaxial films with high magnetization. Applied Physics Letters, 2012, 101, .	1.5	48
99	ZnO, ZnMnO and ZnCoO films grown by atomic layer deposition. Semiconductor Science and Technology, 2012, 27, 074009.	1.0	22
100	ALD grown zinc oxide with controllable electrical properties. Semiconductor Science and Technology, 2012, 27, 074011.	1.0	134
101	Electrical and optical properties of CdHgTe films grown by molecular-beam epitaxy on silicon substrates. Semiconductors, 2012, 46, 1341-1345.	0.2	5
102	Plasma ϵ assisted MBE growth of GaN on Si(111) substrates. Crystal Research and Technology, 2012, 47, 307-312.	0.6	26
103	Fe-Mg interplay and the effect of deposition mode in (Ga,Fe)N doped with Mg. Physical Review B, 2011, 84, .	1.1	21
104	Experimental probing of exchange interactions between localized spins in the dilute magnetic insulator (Ga,Mn)N. Physical Review B, 2011, 84, .	1.1	61
105	ZnO Thin Films of High Crystalline Quality Deposited on Sapphire and GaN Substrates by High Temperature Sputtering. Materials Research Society Symposia Proceedings, 2011, 1315, 1.	0.1	1
106	Synchrotron photoemission study of (Zn,Co)O films with uniform Co distribution. Radiation Physics and Chemistry, 2011, 80, 1046-1050.	1.4	1
107	Role of interface in ferromagnetism of (Zn,Co)O films. Physica Status Solidi (B): Basic Research, 2011, 248, 1596-1600.	0.7	12
108	Oxygen diffusion into GaN from oxygen implanted GaN or Al ϵ 2 ϵ O ϵ 3. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1513-1515.	0.8	11

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109	The uniformity of Al distribution in aluminum-doped zinc oxide films grown by atomic layer deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011, 176, 237-241.	1.7	38
110	Amorphous contact layers on (Cd,Mn)Te crystals. <i>Journal of Crystal Growth</i> , 2011, 320, 1-5.	0.7	6
111	Hafnium dioxide as a passivating layer and diffusive barrier in ZnO/Ag Schottky junctions obtained by atomic layer deposition. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	26
112	Secondary ions mass spectroscopy measurements of dopant impurities in highly stressed InGaN laser diodes. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	14
113	Method of determination of AlGaAsSb layer composition in molecular beam epitaxy processes with regard to unintentional As incorporation. <i>Journal of Applied Physics</i> , 2011, 110, .	1.1	5
114	Multilayer antidiffusion barrier schemes for Schottky and ohmic contact metallisations to InAlN/GaN HEMTs. <i>Materials Research Society Symposia Proceedings</i> , 2011, 1298, 233.	0.1	0
115	Contacts for High-Resistivity (Cd,Mn)Te Crystals. <i>IEEE Transactions on Nuclear Science</i> , 2011, 58, 347-353.	1.2	12
116	Electrical parameters of ZnO films and ZnO-based junctions obtained by atomic layer deposition. <i>Semiconductor Science and Technology</i> , 2011, 26, 085013.	1.0	14
117	ZnO Thin Films Deposited on Sapphire by High Vacuum High Temperature Sputtering. <i>Acta Physica Polonica A</i> , 2011, 119, 686-688.	0.2	3
118	Schottky Junctions Based on the ALD-ZnO Thin Films for Electronic Applications. <i>Acta Physica Polonica A</i> , 2011, 120, A-17-A-21.	0.2	8
119	Cathodoluminescence Measurements at Liquid Helium Temperature of Poly- and Monocrystalline ZnO Films. <i>Acta Physica Polonica A</i> , 2011, 120, A-28-A-30.	0.2	2
120	Synchrotron Photoemission Study of Ferromagnetic (Zn,Co)O Films. <i>Acta Physica Polonica A</i> , 2011, 120, A-40-A-42.	0.2	0
121	SEM, EDS and CL Investigations of ZnMnO and ZnCoO Layers Grown at Low Temperature by Atomic Layer Deposition. <i>Microscopy and Microanalysis</i> , 2010, 16, 810-811.	0.2	7
122	Group IB acceptors in ZnO: experiment and theory. , 2010, , .		1
123	(Cd,Mn)Te detectors for characterization of X-ray emissions generated during laser-driven fusion experiments. <i>Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment</i> , 2010, 624, 649-655.	0.7	7
124	Puzzling magneto-optical properties of ZnMnO films. <i>Optical Materials</i> , 2010, 32, 680-684.	1.7	12
125	Seeded growth of bulk ZnO by chemical vapor transport. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1457-1459.	0.7	17
126	Effects related to deposition temperature of ZnCoO films grown by atomic layer deposition - uniformity of Co distribution, structural, optical, electrical and magnetic properties. <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 1666-1670.	0.7	14

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127	Arsenic incorporation in MBE-grown HgCdTe studied with the use of ion milling. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1618-1620.	0.8	5
128	Contact superconductivity in In-PbTe junctions. <i>Journal of Applied Physics</i> , 2010, 108, 053714.	1.1	14
129	Structural and paramagnetic properties of dilute $\text{Ga}_{1-x}\text{P}_x$. <i>Physical Review B</i> , 2010, 81, .	1.1	70
130	Characterization of Vanadium Doped 4H- and 6H-SiC Grown by PVT Method Using the Open Seed Backside. <i>Materials Science Forum</i> , 2010, 645-648, 21-24.	0.3	2
131	Defect Structure of High-Temperature-Grown GaMnSb/GaSb. <i>Acta Physica Polonica A</i> , 2010, 117, 341-343.	0.2	8
132	Origin of Magnetic Circular Dichroism in GaMnAs: Giant Zeeman Splitting versus Spin Dependent Density of States. <i>Physical Review Letters</i> , 2009, 102, 247202.	2.9	27
133	Response to "Comment on "Common origin of ferromagnetism and band edge Zeeman splitting in GaMnAs at low Mn concentrations" [Appl. Phys. Lett. 94, 156101 (2009)]. <i>Applied Physics Letters</i> , 2009, 94, 156102.	1.5	1
134	Phase Formation in Ti-Al-N MAX-Phase Contacts to GaN. <i>Materials Science Forum</i> , 2009, 615-617, 947-950.	0.3	1
135	On the Formation of Ni-Based Ohmic Contacts to n-Type 4H-SiC. <i>Materials Science Forum</i> , 2009, 615-617, 573-576.	0.3	19
136	The ratio of interstitial to substitutional site occupation by Mn atoms in GaAs estimated by EXAFS. <i>Radiation Physics and Chemistry</i> , 2009, 78, S80-S85.	1.4	8
137	Effect of processing on microstructure of Si:Mn. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009, 159-160, 99-102.	1.7	8
138	Nitride-based quantum structures and devices on modified GaN substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009, 206, 1130-1134.	0.8	17
139	Coexistence of ferromagnetism and quantum Hall effect in Mn modulation-doped two-dimensional hole systems. <i>Journal of Crystal Growth</i> , 2009, 311, 2160-2162.	0.7	13
140	Characterization of 6H-SiC Single Crystals Grown by PVT Method Using Different Source Materials and Open or Closed Seed Backside. <i>Materials Science Forum</i> , 2009, 615-617, 19-22.	0.3	3
141	Diluted magnetic semiconductors based on II-VI, III-VI, and IV-VI compounds. <i>Low Temperature Physics</i> , 2009, 35, 62-70.	0.2	9
142	Ferromagnetic Transition in $\text{Ge}_{1-x}\text{Mn}_x\text{Te}$ Layers. <i>Acta Physica Polonica A</i> , 2009, 116, 904-906.	0.2	9
143	ZnCoO Films by Atomic Layer Deposition - Influence of a Growth Temperature on Uniformity of Cobalt Distribution. <i>Acta Physica Polonica A</i> , 2009, 116, 921-923.	0.2	6
144	The influence of the growth temperature and interruption time on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. <i>Journal of Crystal Growth</i> , 2008, 310, 2785-2792.	0.7	24

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145	Magneto spectroscopy of symmetric and anti-symmetric states in double quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 894-906.	1.3	6
146	Vertically stacked non-volatile memory devices – material considerations. Microelectronic Engineering, 2008, 85, 2434-2438.	1.1	37
147	Periodic Mg distribution in GaN:Mg and the effect of annealing on structural and optical properties. Applied Surface Science, 2008, 255, 731-733.	3.1	5
148	The Influence of Growth Temperature on Oxygen Concentration in GaN Buffer Layer. Materials Research Society Symposia Proceedings, 2008, 1068, 1.	0.1	1
149	Technique of making good electrical contacts to high resistivity (Cd,Mn) Te crystals. , 2008, , .		0
150	Effects of magnetic ions on optical properties: the case of (Ga, Fe)N. Journal of Physics Condensed Matter, 2008, 20, 454222.	0.7	0
151	Substrate misorientation induced strong increase in the hole concentration in Mg doped GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2008, 93, 172117.	1.5	31
152	Ti-Al-N MAX Phase a Candidate for Ohmic Contacts to n-GaN. Acta Physica Polonica A, 2008, 114, 1061-1066.	0.2	16
153	Magnetic Properties of Epitaxial (Ge,Mn)Te Thin Films with Varying Crystal Stoichiometry. Acta Physica Polonica A, 2008, 114, 1159-1165.	0.2	10
154	Ferromagnetism of Narrow-Gap Ge _{1-x} Sn _x Mn _y Te and Layered In _{1-x} Mn _x Se Semiconductors. Acta Physica Polonica A, 2008, 114, 1219-1227.	0.2	3
155	ZnCoO Films Obtained at Low Temperature by Atomic Layer Deposition Using Organic Zinc and Cobalt Precursors. Acta Physica Polonica A, 2008, 114, 1235-1240.	0.2	6
156	XANES Studies of Mn K and L _{2,3} Edges in the (Ga, Mn)As Layers Modified by High Temperature Annealing. Acta Physica Polonica A, 2008, 114, 357-366.	0.2	6
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